

# **NHDTA114/124/144EU** series

80 V, 100 mA PNP resistor-equipped transistors

Rev. 1 — 22 July 2020

**Product data sheet** 

# 1. General description

PNP Resistor-Equipped Transistor (RET) family in a very small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package.

**Table 1. Product overview** 

Type number	R1	R2		Package	NPN complement:
	kΩ	kΩ	Nexperia	JEITA	
NHDTA114EU	10	10	SOT323	SC-70	NHDTC114EU
NHDTA124EU	22	22			NHDTC124EU
NHDTA144EU	47	47			NHDTC144EU

# 2. Features and benefits

- · 100 mA output current capability
- High breakdown voltage
- · Built-in resistors
- · Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

# 3. Applications

- · Digital applications
- · Cost saving alternative for BC856 series in digital applications
- Controlling IC inputs
- Switching loads

# 4. Quick reference data

#### Table 2. Quick reference data

T<sub>amb</sub> = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-80	V
I <sub>O</sub>	output current		-	-	-100	mA



# 5. Pinning information

### **Table 3. Pinning**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)	<u></u> 3	
2	GND	GND (emitter)		R1
3	0	output (collector)		
				GND
				aaa-019606

# 6. Ordering information

## **Table 4. Ordering information**

Type number	Package					
	Name	Description	Version			
NHDTA114EU	SC-70	plastic surface-mounted package; 3 leads	SOT323			
NHDTA124EU						
NHDTA144EU						

# 7. Marking

## Table 5. Marking

Type number	Marking code [1]				
NHDTA114EU	5F%				
NHDTA124EU	5J%				
NHDTA144EU	5L%				

[1] % = placeholder for manufacturing site code

# 8. Limiting values

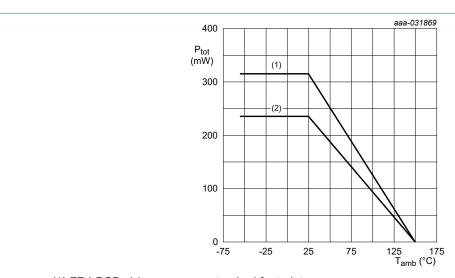
#### Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

T<sub>amb</sub> = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Max	Unit		
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-80	V		
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-80	V		
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-10	V		
V <sub>I</sub>	input voltage							
	NHDTA114EU			-40	+10	V		
	NHDTA124EU			-60	+10	V		
	NHDTA144EU			-80	+10	V		
Io	output current			-	-100	mA		
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	235	mW		
			[2]	-	315	mW		
Tj	junction temperature			-	150	°C		
T <sub>amb</sub>	ambient temperature			-55	150	°C		
T <sub>stg</sub>	storage temperature			-65	150	°C		

- [1] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit-Board (PCB);4-layer copper; tin-plated and standard footprint.



- (1) FR4 PCB, 4-layer copper, standard footprint
- (2) FR4 PCB, single-sided copper, standard footprint

Fig. 1. Power derating curves for SOT323 (SC-70)

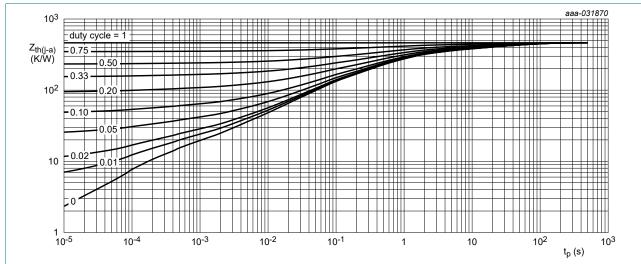
# 9. Thermal characteristics

#### **Table 7. Thermal characteristics**

 $T_{amb}$  = 25 °C unless otherwise specified.

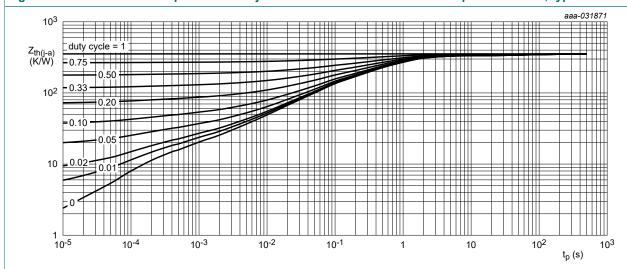
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	532	K/W
			[2]	-	-	397	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	150	K/W

- [1] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), 4-layer copper, tin-plated and standard footprint.



FR4 PCB, single-sided copper, tin-plated and standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, tin-plated and standard footprint

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

# 10. Characteristics

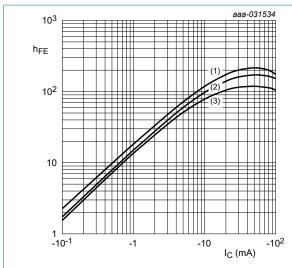
#### **Table 8. Characteristics**

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit			
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	I <sub>C</sub> = -100 μA; I <sub>E</sub> = 0 A		-80	-	-	V			
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	I <sub>C</sub> = -2 mA; I <sub>B</sub> = 0 A		-80	-	-	V			
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -80 \text{ V}; I_{E} = 0 \text{ A}$		-	-	-100	nA			
I <sub>CEO</sub>	collector-emitter cut-off	V <sub>CE</sub> = -60 V; I <sub>B</sub> = 0 A		-	-	-100	nA			
	current	V <sub>CE</sub> = -60 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	-5	μΑ			
I <sub>EBO</sub>	emitter-base cut-off curr	emitter-base cut-off current								
	NHDTA114EU	V <sub>EB</sub> = -7 V; I <sub>C</sub> = 0 A		-	-	-600	μA			
	NHDTA124EU		-	-	-270	μA				
	NHDTA144EU		-	-	-130	μA				
h <sub>FE</sub>	DC current gain									
	NHDTA114EU	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -10 mA			-	-				
	NHDTA124EU				-	-				
	NHDTA144EU		100	-	-					
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -10 mA; I <sub>B</sub> = -0.5 mA		-	-	-100	mV			
$V_{I(off)}$	off-state input voltage	V <sub>CE</sub> = -5 V ; I <sub>C</sub> = -100 μA		-	-1.15	-0.8	V			
V <sub>I(on)</sub>	on-state input voltage						_			
	NHDTA114EU	$V_{CE} = -0.3 \text{ V}$ ; $I_{C} = -10 \text{ mA}$		-2.5	-1.8	-	V			
	NHDTA124EU			-3	-2.3	-	V			
	NHDTA144EU			-5	-3.3	-	V			
R1	bias resistor 1 (input)		[1]							
	NHDTA114EU			7	10	13	kΩ			
	NHDTA124EU	1		15.4	22	28.6	kΩ			
	NHDTA144EU	1		33	47	61	kΩ			
R2/R1	bias resistor ratio		[1]	8.0	1	1.2				
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -10 mA; f = 100 MHz	[2]	-	150	-	MHz			
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = i <sub>e</sub> = 0 A; f = 1 MHz		-	-	3	pF			

<sup>[1]</sup> See section "Test information" for resistor calculation and test conditions

<sup>[2]</sup> Characteristics of built-in transistor

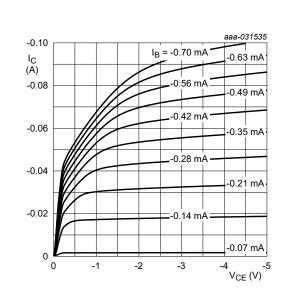


$$V_{CE} = -5 V$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

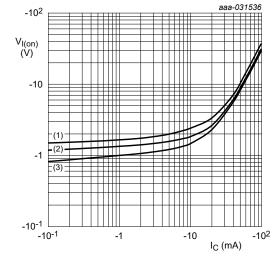
(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 4. NHDTA114EU: DC current gain as a function of collector current; typical values



 $T_{amb}$  = 25 °C

Fig. 5. NHDTA114EU: Collector current as a function of collector-emitter voltage; typical values



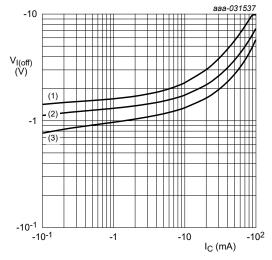
$$V_{CE}$$
 = -0.3  $V$ 

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. NHDTA114EU: On-state input voltage as a function of collector current; typical values



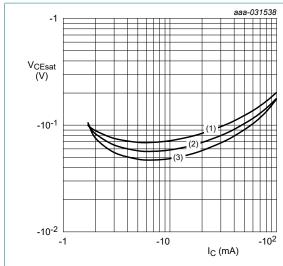
$$V_{CE} = -5 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. NHDTA114EU: Off-state input voltage as a function of collector current; typical values



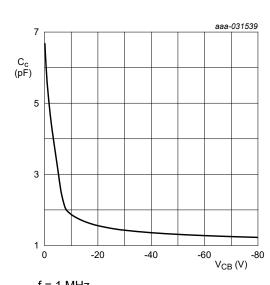
 $I_{\rm C}/I_{\rm B} = 20$ 

(1)  $T_{amb}$  = 100 °C

(2) T<sub>amb</sub> = 25 °C

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

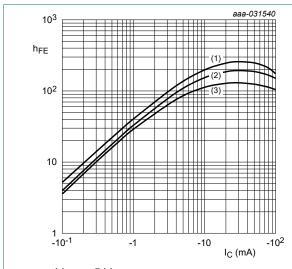
Fig. 8. NHDTA114EU: Collector-emitter saturation voltage as a function of collector current; typical values



f = 1 MHz

 $T_{amb}$  = 25 °C

Fig. 9. NHDTA114EU: Collector capacitance as a function of collector-base voltage; typical values



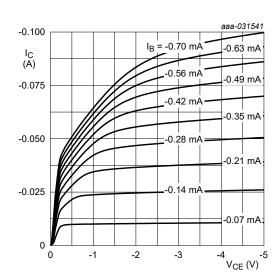
 $V_{CE} = -5 V$ 

(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

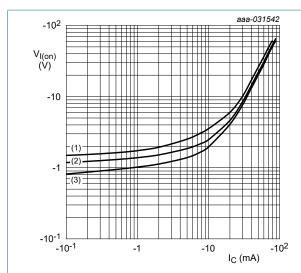
(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 10. NHDTA124EU: DC current gain as a function of collector current; typical values



T<sub>amb</sub> = 25 °C

Fig. 11. NHDTA124EU: Collector current as a function of collector-emitter voltage; typical values



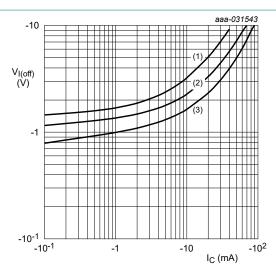
$$V_{CE}$$
 = -0.3  $V$ 

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 12. NHDTA124EU: On-state input voltage as a function of collector current; typical values



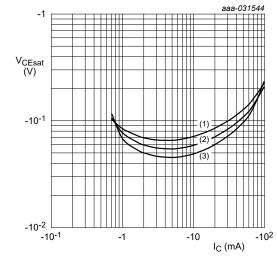
$$V_{CE} = -5 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 13. NHDTA124EU: Off-state input voltage as a function of collector current; typical values



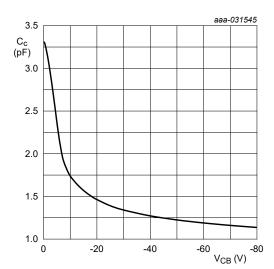
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

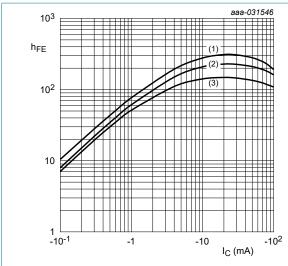
(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 14. NHDTA124EU: Collector-emitter saturation voltage as a function of collector current; typical values



f = 1 MHz

Fig. 15. NHDTA124EU: Collector capacitance as a function of collector-base voltage; typical values

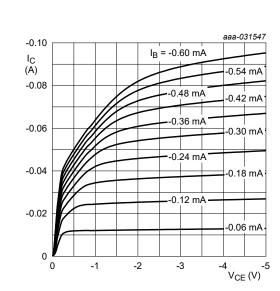


$$V_{CE} = -5 V$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

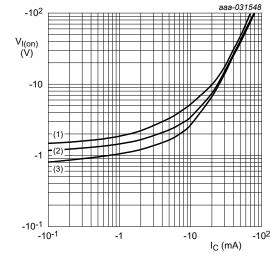
(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 16. NHDTA144EU: DC current gain as a function of collector current; typical values



 $T_{amb}$  = 25 °C

Fig. 17. NHDTA144EU: Collector current as a function of collector-emitter voltage; typical values



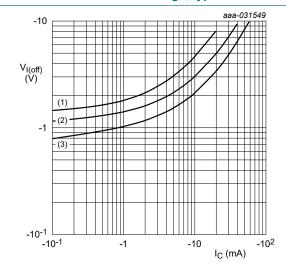
$$V_{CE} = -0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 18. NHDTA144EU: On-state input voltage as a function of collector current; typical values

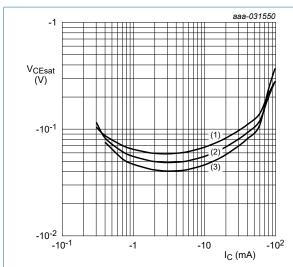


$$V_{CE} = -5 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

Fig. 19. NHDTA144EU: Off-state input voltage as a function of collector current; typical values

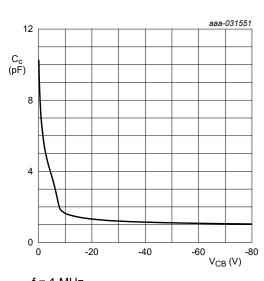


$$I_{\rm C}/I_{\rm B} = 20$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

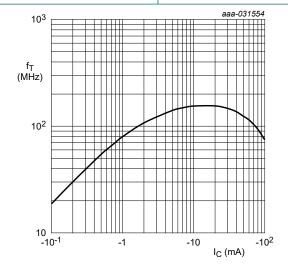
(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 20. NHDTA144EU: Collector-emitter saturation voltage as a function of collector current; typical values



$$f = 1 MHz$$
  
 $T_{amb} = 25 °C$ 

Fig. 21. NHDTA144EU: Collector capacitance as a function of collector-base voltage; typical values of built-in transistor



f = 100 MHz

 $V_{CE} = -5 V$ 

T<sub>amb</sub> = 25 °C

Fig. 22. Transition frequency as a function of collector current; typical values of built-in transistor

# 11. Test information

# **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

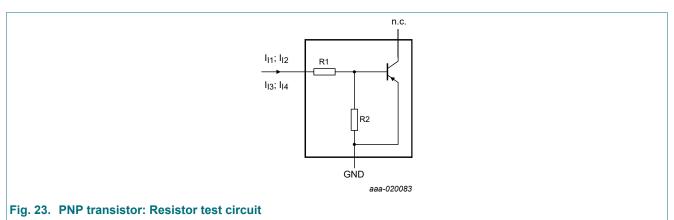
### **Resistor calculation**

Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I12) - V(I11)}{I12 - I11}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

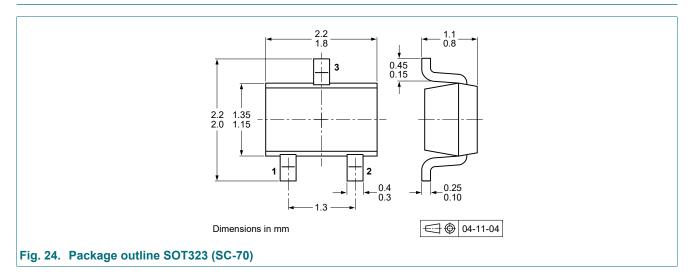


# Resistor test conditions

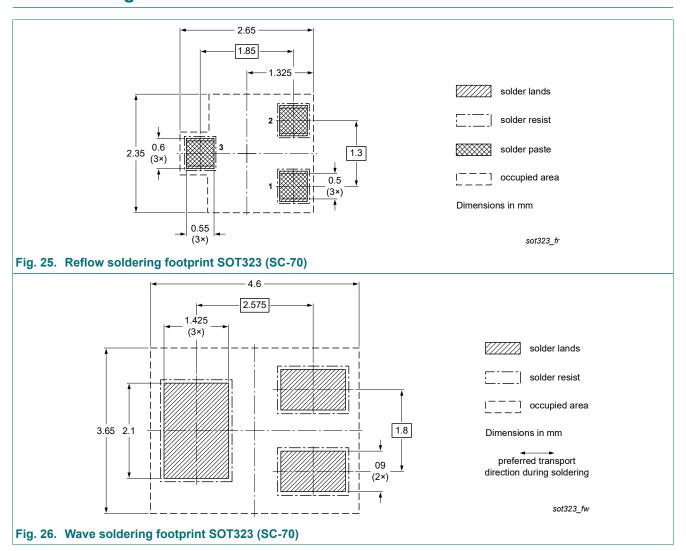
**Table 9. Resistor test conditions** 

Type number	R1 (kΩ)	R2 (kΩ)	Test conditions				
			I <sub>I1</sub>	I <sub>I2</sub>	I <sub>13</sub>	I <sub>14</sub>	
NHDTA114EU	10	10	-800 μΑ	-1.1 mA	350 µA	450 µA	
NHDTA124EU	22	22	-550 μΑ	-750 μA	150 µA	230 μΑ	
NHDTA144EU	47	47	-250 μA	-350 μΑ	55 µA	105 μΑ	

# 12. Package outline



# 13. Soldering



# 14. Revision history

## Table 10. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NHDTA114_124_144EU_SER v.1	20200722	Product data sheet	-	-

# 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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NSBC114YF3T5G NSBC123TF3T5G SMUN5235T1G SMUN5330DW1T1G SSVMUN5312DW1T2G RN1303(TE85L,F)

RN4605(TE85L,F) TTEPROTOTYPE79 DDTC114EUAQ-7-F EMH15T2R SMUN2214T3G SMUN5335DW1T1G NSBC114TF3T5G

NSBC143ZPDP6T5G NSVMUN5113DW1T3G SMUN5230DW1T1G SMUN5133T1G SMUN2214T1G DTC114EUA-TP

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DCX115EK-7-F DTC113EM3T5G NSVMUN5135DW1T1G NSVMUN2237T1G